

## MJE180/181/182

Low Power Audio Amplifier Low Current High Speed Switching Applications



## **NPN Epitaxial Silicon Transistor**

### **Absolute Maximum Ratings** T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage : MJE180	60	V
	: MJE181	80	V
	: MJE182	100	V
V <sub>CEO</sub>	Collector-Emitter Voltage : MJE180	40	V
	: MJE181	60	V
	: MJE182	80	V
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
I <sub>C</sub>	Collector Current (DC)	3	А
I <sub>CP</sub>	Collector Current (Pulse)	6	А
I <sub>B</sub>	Base Current	1	А
P <sub>C</sub>	Collector Dissipation (T <sub>a</sub> =25°C)	1.5	W
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	12.5	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 65 ~ 150	°C

## **Electrical Characteristics** T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV <sub>CEO</sub>	Collector -Emitter Breakdown Voltage				
	: MJE180	$I_C = 10 \text{mA}, I_B = 0$	40		V
	: MJE181		60		V
	: MJE182		80		V
I <sub>CBO</sub>	Collector Cut-off Current : MJE180	$V_{CB} = 60V, I_B = 0$		0.1	μΑ
	: MJE181	$V_{CB} = 80V, I_{E} = 0$		0.1	μΑ
	: MJE182	$V_{CB} = 100V, I_{E} = 0$		0.1	μΑ
	: MJE180	$V_{CB} = 60V, I_{E} = 0 @ T_{C} = 150^{\circ}C$		0.1	mA
	: MJE181	$V_{CB} = 80V, I_{E} = 0 @ T_{C} = 150^{\circ}C$		0.1	mA
	: MJE182	$V_{CB} = 100V, I_{E} = 0 @ T_{C} = 150^{\circ}C$		0.1	mA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{BE} = 7V, I_{C} = 0$		0.1	μΑ
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 1V, I_{C} = 100mA$	50	250	
		$V_{CE} = 1V, I_{C} = 500mA$	30		
		$V_{CE} = 1V, I_{C} = 1.5A$	12		
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$		0.3	V
		$I_C = 1.5A, I_B = 150mA$		0.9	V
		$I_C = 3A, I_B = 600mA$		1.7	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	$I_C = 1.5A, I_B = 150mA$		1.5	V
		$I_C = 3A$ , $I_B = 600mA$		2.0	V
V <sub>BE</sub> (on)	Base-Emitter ON Voltage	V <sub>CE</sub> = 1V, I <sub>C</sub> = 500mA		1.2	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = 10V, I <sub>C</sub> = 100mA	50		MHz
C <sub>ob</sub>	Output Capacitance	$V_{CB} = 10V, I_E = 0, f = 0.1MHz$		30	pF

# **Typical Characteristics**

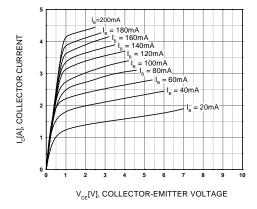


Figure 1. Static Characteristic

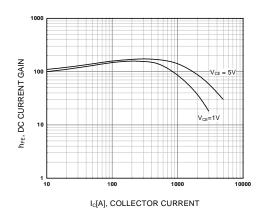


Figure 2. DC current Gain

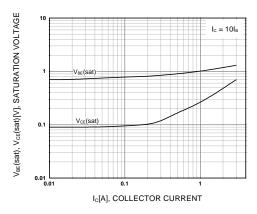


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

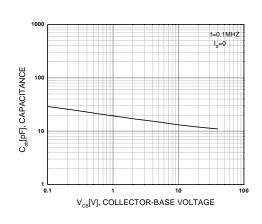


Figure 4. Collector Output Capacitance

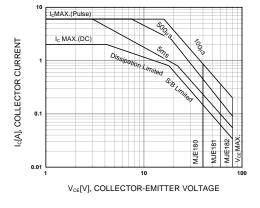


Figure 5. Safe Operating Area

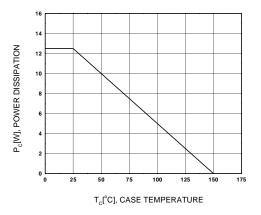
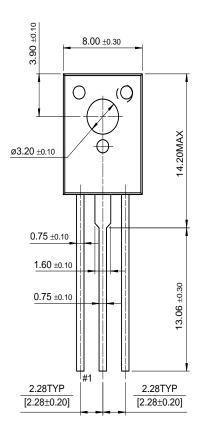


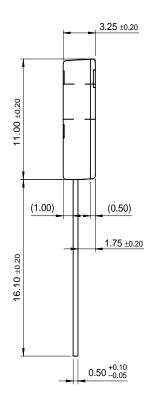
Figure 6. Power Derating

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# **Package Demensions**

TO-126







Dimensions in Millimeters

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